Thyristor Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-00-449-4229

view Online at https://aerobasegroup.com/nsn/5961-00-449-4229
Inclosure Material:
Metal
Overall Length:
0.505 inches
Overall Diameter:
0.650 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Overall Width Across Flats:
0.562 inches
Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
800.0 breakover voltage, dc
Current Rating Per Characteristic:
0.10 amperes forward current, total rms peak
Power Rating Per Characteristic:
2.0 watts small-signal input power, common-collector outside diameter
Maximum Operating Tempurature Per Measurement Point:
120.0 degrees celsius junction
Special Features:
Junction pattern arrangement: pnpn
Thread Series Designator:
Unf
Terminal Type And Quantity:
1 threaded stud and 2 tab, solder lug
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

NSN 5961-00-449-4229

Thyristor Semiconductor Device - Page 2 of 2

Fiig: A110a0

